MPSA13, MPSA14

MPSA14 is a Preferred Device

Darlington Transistors

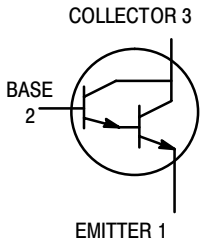
NPN Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available*



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CES}	30	Vdc
Collector−Base Voltage	V_{CBO}	30	Vdc
Emitter−Base Voltage	V_{EBO}	10	Vdc
Collector Current − Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 625 5.0	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.5 12	 W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

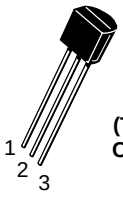
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/mW
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/mW

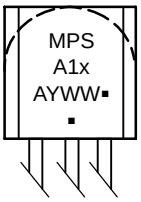
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



TO−92
(TO−226AA)
CASE 29−11
STYLE 1



x = 3 or 4
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = 100 μAdc, I_B = 0)		$V_{(BR)CES}$	30	−	Vdc
Collector Cutoff Current (V_{CB}= 30 Vdc, I_E = 0)		I_{CBO}	−	100	nAdc
Emitter Cutoff Current (V_{EB}= 10 Vdc, I_C = 0)		I_{EBO}	−	100	nAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain		h_{FE}			−
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MPSA13		5,000	−	
	MPSA14		10,000	−	
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	MPSA13		10,000	−	
	MPSA14		20,000	−	
Collector−Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	−	1.5	Vdc
Base−Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	−	2.0	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (Note 2) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	125	−	MHz

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.
2. $f_T = |h_{fe}| \bullet f_{test}$.

ORDERING INFORMATION

Device	Package	Shipping†
MPSA13	TO−92	5000 Units / Box
MPSA13G	TO−92 (Pb−Free)	5000 Units / Box
MPSA13RLRA	TO−92	2000 / Tape & Reel
MPSA13RLRAG	TO−92 (Pb−Free)	2000 / Tape & Reel
MPSA13RLRM	TO−92	2000 / Ammo Pack
MPSA13RLRMG	TO−92 (Pb−Free)	2000 / Ammo Pack
MPSA13RLRP	TO−92	2000 / Ammo Pack
MPSA13RLRPG	TO−92 (Pb−Free)	2000 / Ammo Pack
MPSA13ZL1	TO−92	2000 / Ammo Pack
MPSA13ZL1G	TO−92 (Pb−Free)	2000 / Ammo Pack
MPSA14	TO−92	5000 Units / Box
MPSA14G	TO−92 (Pb−Free)	5000 Units / Box
MPSA14RLRA	TO−92	2000 / Tape & Reel
MPSA14RLRAG	TO−92 (Pb−Free)	2000 / Tape & Reel
MPSA14RLRP	TO−92	2000 / Ammo Pack
MPSA14RLRPG	TO−92 (Pb−Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

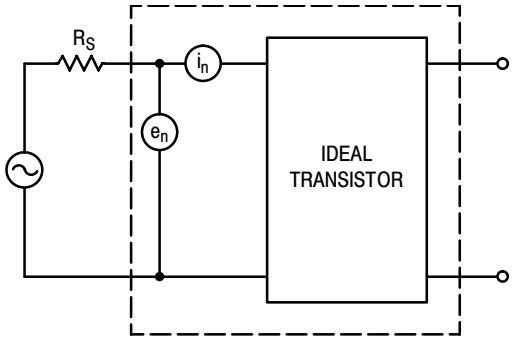


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

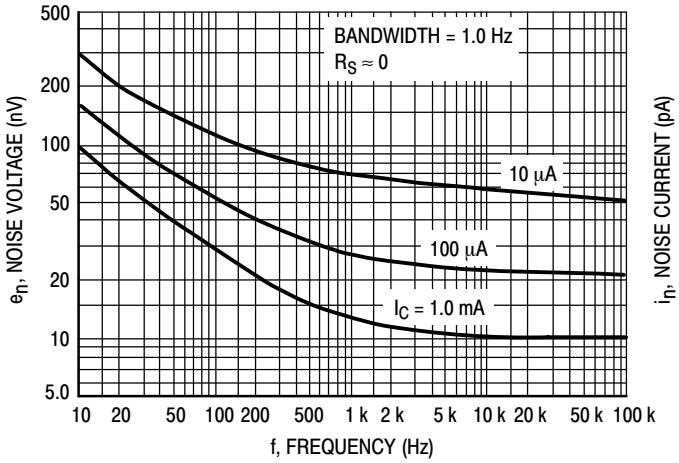


Figure 2. Noise Voltage

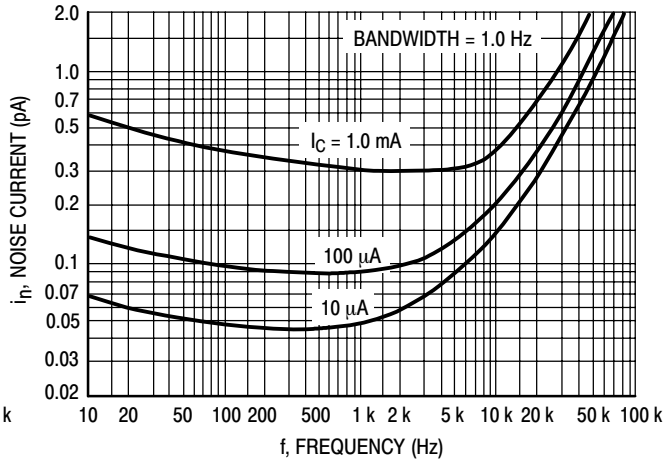


Figure 3. Noise Current

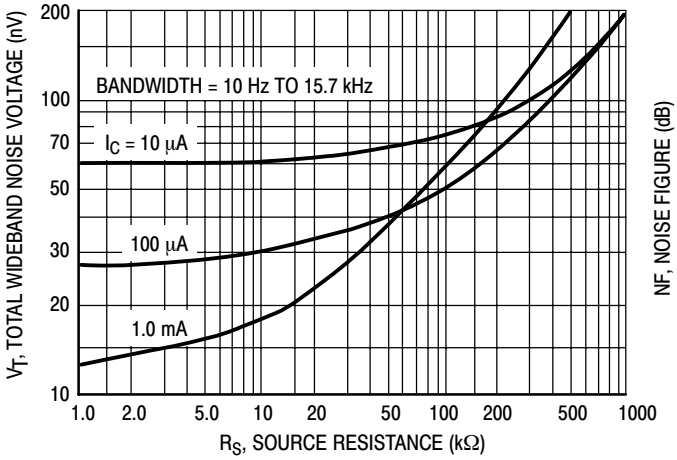


Figure 4. Total Wideband Noise Voltage

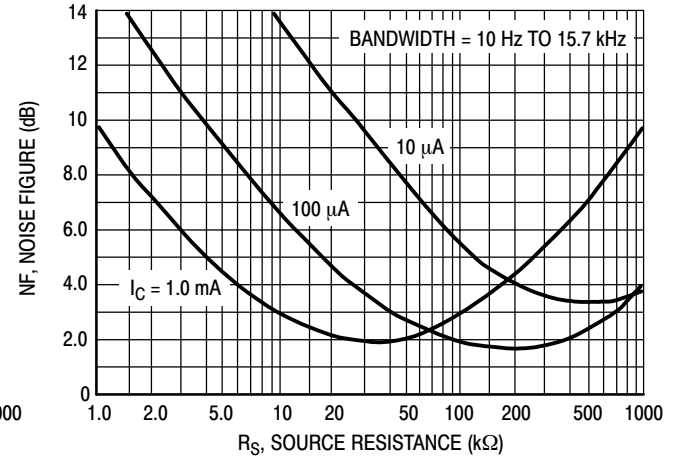


Figure 5. Wideband Noise Figure

SMALL−SIGNAL CHARACTERISTICS

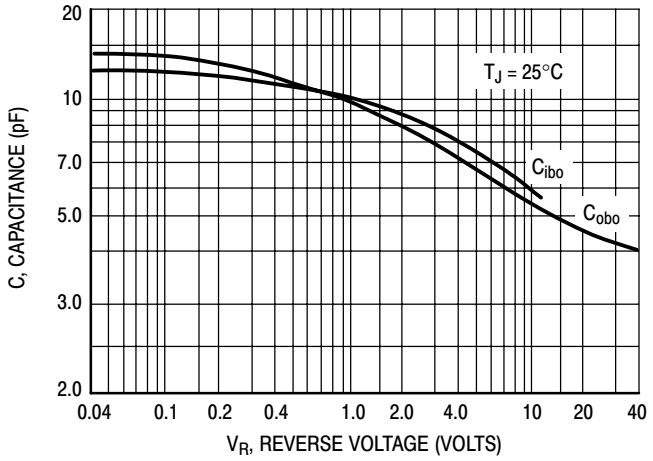


Figure 6. Capacitance

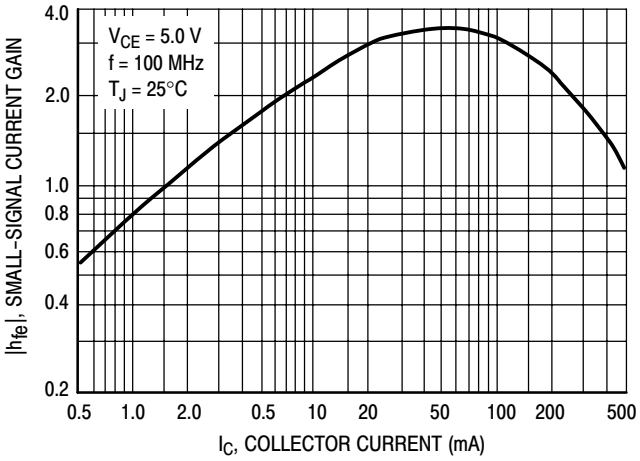


Figure 7. High Frequency Current Gain

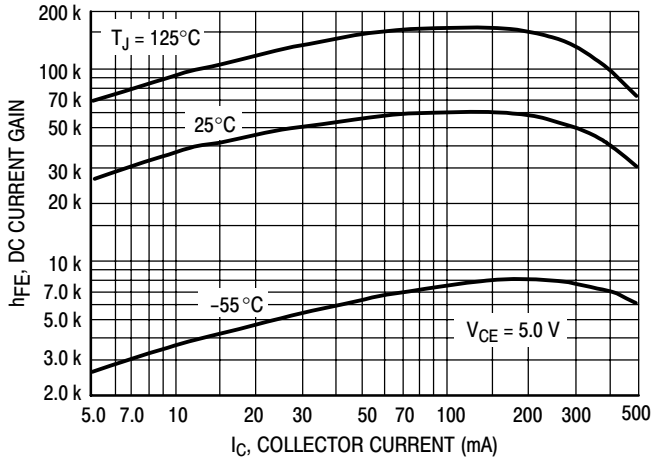


Figure 8. DC Current Gain

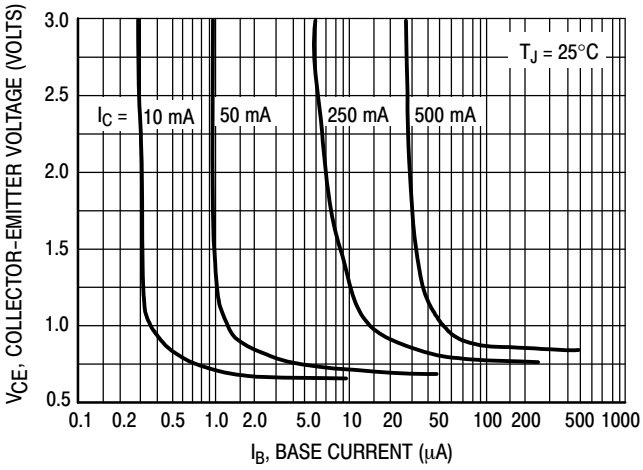


Figure 9. Collector Saturation Region

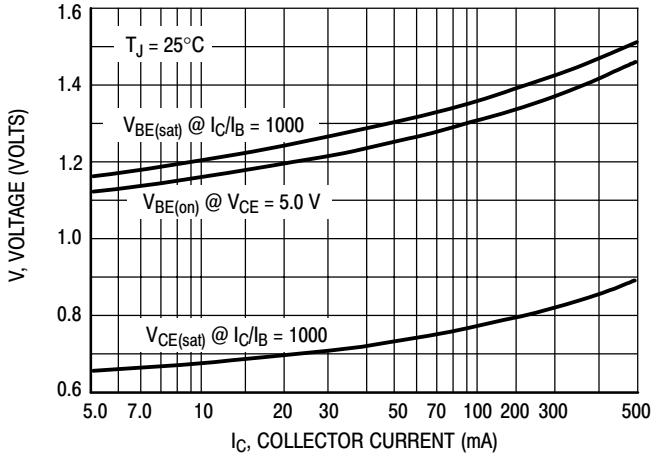


Figure 10. “On” Voltages

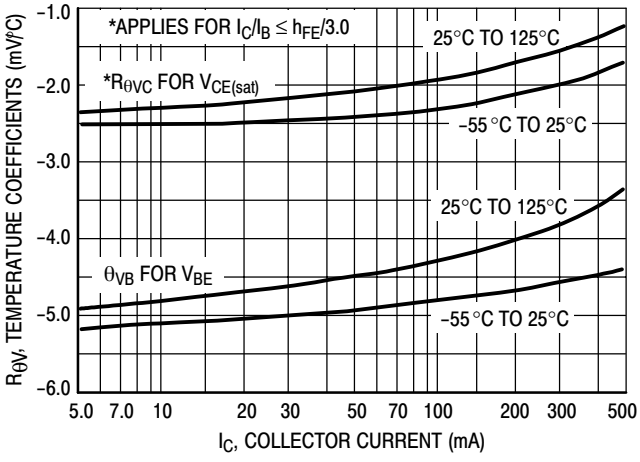


Figure 11. Temperature Coefficients

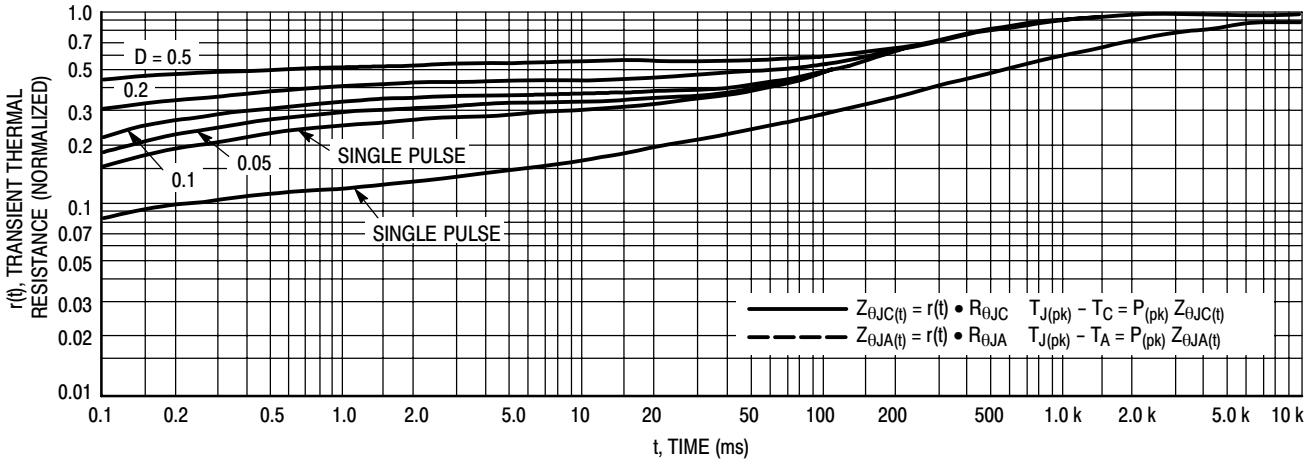


Figure 12. Thermal Response

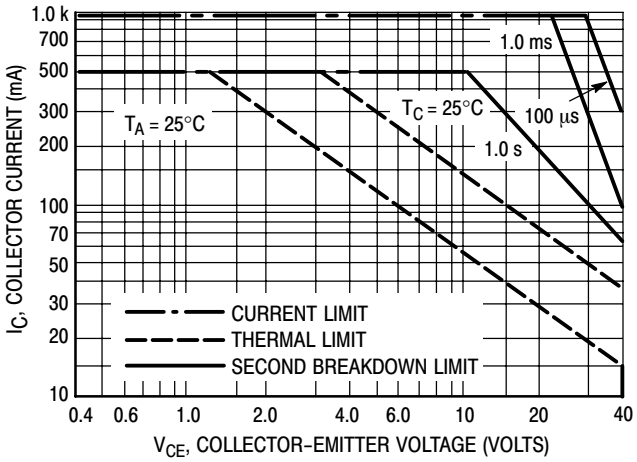
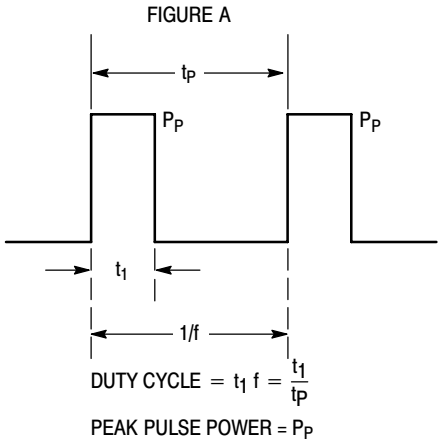


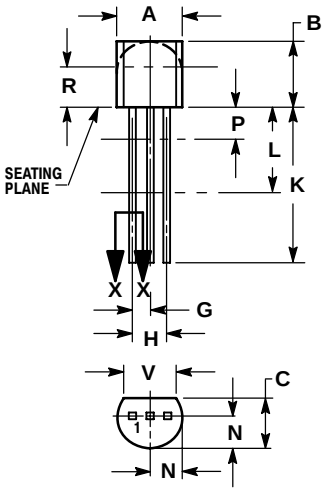
Figure 13. Active Region Safe Operating Area

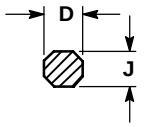


Design Note: Use of Transient Thermal Resistance Data

PACKAGE DIMENSIONS

TO−92
TO−226AA
CASE 29−11
ISSUE AL





SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

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